

# INFORMATION DISCLOSURE CITATION

(Use several sheets if necessary)

Docket Number (Optional)

FIS92000039

Application Number

Applicant(s)

KHARE ET AL.

Filing Date

Group Art Unit

## U.S. PATENT DOCUMENTS

*EXAMINER INITIAL	REF	DOCUMENT NUMBER	DATE	NAME	CLASS	SUBCLASS	FILING DATE IF APPROPRIATE
BJ		5,578,848	11/26/1996	Kwong et al.	257	296	
BJ		5,674,788	10/7/1997	Wristers et al.	437	239	
BJ		5,861,651	1/19/1999	Brasen et al.	438	253	
BJ		5,880,040	3/9/1999	Sun et al.	257	411	
BJ		6,017,791	1/25/2000	Wang et al.	438	253	
BJ		6,087,236	7/11/2000	Chau et al.	438	301	
BJ		6,110,842	8/29/2000	Okuno et al.	438	746	
BJ		6,140,024	10/31/2000	Misium et al.	430	314	

## FOREIGN PATENT DOCUMENTS

	REF	DOCUMENT NUMBER	DATE	COUNTRY	CLASS	SUBCLASS	Translation	
							YES	NO

## OTHER DOCUMENTS (Including Author, Title, Date, Pertinent Pages, Etc.)

BJ		Lucovsky, G., "Ultrathin Nitrided Gate Dielectrics: Plasma Processing, Chemical Characterization, Performance and Reliability," IBM JOURNAL OF RESEARCH & DEVELOPMENT, Vol. 43, No. 3, 1999, pages 1 - 27
BJ		Gusev, E.P.; Lu, H.C.; Garfunkel, E. L.; Gustafsson, T.; and Green, M. L., "Growth and Characterization of Ultrathin Nitrided Silicon Oxide Film," IBM JOURNAL OF RESEARCH AND DEVELOPMENT, Vol. 43, No. 3, 1999, pages 1-22.

EXAMINER

Fernando Toledo

DATE CONSIDERED

February 19, 2002

EXAMINER: Initial if citation considered, whether or not citation is in conformance with MPEP Section 609; Draw line through citation if not in conformance and not considered. Include copy of this form with next communication to applicant.